



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

3DK2222A

TRANSISTOR(NPN)

FEATURE

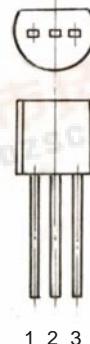
Power dissipation

 P_{CM} : 0.625 W($T_{amb}=25^{\circ}C$)**TO-92**

1. Emitter

2. Base

3. Collector

**MAXIMUM RATINGS*** $T_A=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	75	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	600	mA
P_D	Total Device Dissipation	625	mW
T_J	Junction Temperature	150	°C
T_{stg}	Junction and Storage Temperature	-55-150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

ELECTRICAL CHARACTERISTICS($T_{amb}=25^{\circ}C$ unless otherwise specified)

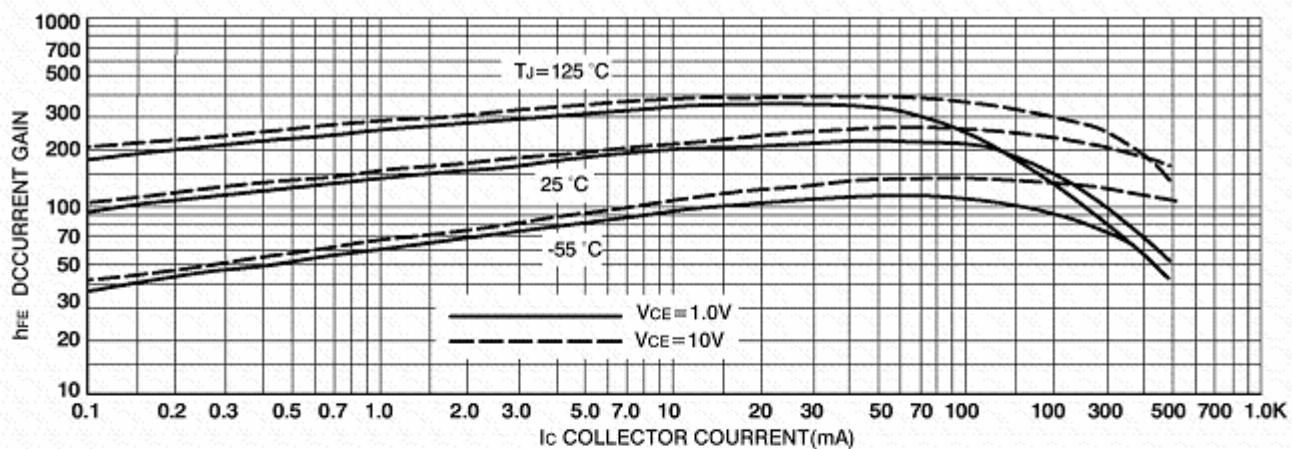
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	$I_C= 10\mu A, I_E=0$	75		V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	$I_C= 10 mA, I_B=0$	40		V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	$I_E= 10\mu A, I_C=0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB}= 60 V, I_E=0$		10	nA
Collector cut-off current	I_{CEX}	$V_{CE}= 60 V, V_{EB(OFF)}=3V$		10	nA
Emitter cut-off current	I_{EBO}	$V_{EB}= 3 V, I_C=0$		10	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=10 V, I_C= 150mA$	100	300	
	$h_{FE(2)}$	$V_{CE}=10 V, I_C= 0.1mA$	40		
	$h_{FE(3)}$	$V_{CE}=10 V, I_C= 500mA$	42		
Collector-emitter saturation voltage	$V_{CE(sat)(1)}$	$I_C= 500 mA, I_B= 50 mA$		0.6	V
	$V_{CE(sat)(2)}$	$I_C= 150 mA, I_B= 15 mA$		0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C= 500 mA, I_B= 50 mA$		1.2	V
Storage time	t_{stg}	$V_{CC}=30V, I_C=150mA, I_{B1}=I_{B2}=15mA$		225	ns
Transition frequency	f_T	$V_{CE}= 20 V, I_C= 20mA, f = 100MHz$	300		MHz

CLASSIFICATION OF $h_{FE(1)}$

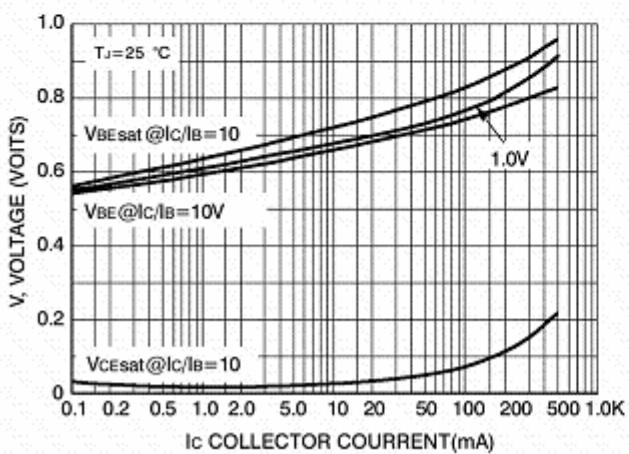
Rank	L	H
	100-200	200-300

Typical Characteristics

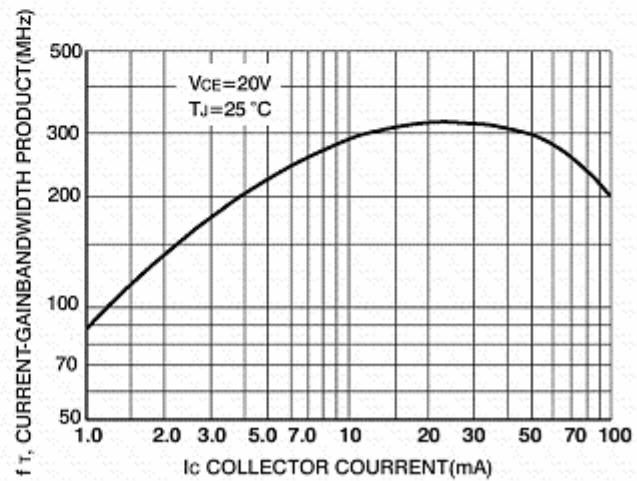
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DC Current Gain



"On" Voltages



Current-Gain Bandwidth Product

